Erratum to: Study of various technological parameters on the C-V_g and the G-V_g characteristics of MOS structures

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After publication of the paper, the author noticed that eq. (1),

$$Y = G_{\text{MOS}} + j\omega C_{\text{MOS}} = \frac{1}{R_s + \frac{1}{j\omega C_{\text{ox}}} + \frac{1}{(R_p + \frac{1}{j\omega C_{\text{sc}}})}}, \quad (1)$$

was erroneously given. It should now read

$$Y = G_{\text{MOS}} + j\omega C_{\text{MOS}} = \frac{1}{R_s + \frac{1}{j\omega C_{\text{ox}}} + \frac{1}{(j\omega C_{\text{sc}} + \frac{1}{R_p})}}. \quad (1)$$

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